

AMENDMENTS TO THE CLAIMS:

12. (Cancelled)

13. (Cancelled)

14. A method as defined in claim 13, wherein:

A method for forming an emitter contact for a bipolar junction transistor comprising the steps of:

providing a silicon substrate having a collector region, a base region within said collector region, and an emitter region within said base region;

depositing a base polysilicon layer on said silicon substrate in contact with said base region, and defining an aperture with side walls exposing said base and emitter regions of said silicon substrate; said step of depositing a base polysilicon layer further includes the steps of:

depositing a layer of oxide onto said layer of base polysilicon; and
forming said aperture through both of said layers of base polysilicon and oxide;

forming a spacer extending upwardly from said silicon substrate and to cover said side walls, said spacer covering said base region and partially covering said emitter region; and

forming an emitter polysilicon layer positioned within said aperture in engagement with said emitter region, said spacer and said substrate, said step of forming an emitter polysilicon layer further includes the steps of:

depositing a layer of emitter polysilicon onto said oxide and into said aperture; and

etching back said layer of emitter polysilicon to stop on a top surface of said oxide layer.

15. (Cancelled)

16. A method as defined in claim 14 12, wherein the step of depositing the emitter polysilicon further includes the steps of:

in situ doping the emitter polysilicon up to a level of $1E21$ atoms per cubic centimeter with a dopant material; and

performing a rapid thermal anneal to diffuse the dopant material.
